

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	1002	park near sang.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	7	1 and (metal near3 dop\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	2	(metal near3 dop\$3) near15 ((copper or alloy) near (wiring))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	2374	(metal) near15 ((copper or alloy) near3 (wiring))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	0	(metal near dopinr) near15 ((copper or alloy) near3 (wiring))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	0	(metal near doping) near15 ((copper or alloy) near3 (wiring))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	109	(metal) near15 ((copper or alloy) near3 (wiring)) near25 (copper near alloy)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	3	(metal) near15 ((copper or alloy) near3 (wiring)) near25 (copper near alloy) near15 (metal near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	15	(metal) near15 ((copper or alloy) near3 (wiring)) near25 (copper near alloy) near15 (oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	12	(copper near wiring) near25 (copper near alloy) near15 (oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	2	(metal near3 doping) near10 ((wiring) near (copper or cu))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	3	(doping) near10 ((wiring) near (copper or cu))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	14	(dop\$3) near10 ((wiring) near (copper or cu))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	987	(metal or mg or cd or be or sn or pd) near10 ((wiring) near (copper or cu))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	149	14 and (metal near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	22	(metal or mg or cd or be or sn or pd) near10 ((wiring) near (copper or cu)) near15 (metal near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	1	(copper near anti-diffusion) near10 ((wiring) near (copper or cu)) near15 (metal near oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	1	(copper near anti near diffusion) near10 ((wiring) near (copper or cu)) near15 (metal near oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	1	(copper near anti near diffusion) near10 ((wiring) near5 (copper or cu)) near15 (metal near oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L20	1	(anti-diffusion) near10 ((wiring) near (copper or cu)) near15 (metal near oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	9	(copper) near10 ((wiring) near (copper or cu)) near15 (metal near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	6	(copper near alloy) near10 (wiring) near15 (metal near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	1	(implant\$3) near10 (wiring) near15 (metal near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	9	(dop\$3) near10 (wiring) near15 (metal near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	14	(dop\$3) near25 (anti-diffusion)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20050023698 A1	Method for fabricating metal wiring and semiconductor device having the same
2			US 20050009331 A1	Method of forming copper wiring in semiconductor device
3			US 20040089952 A1	Structure and method for charge sensitive electrical devices
4			US 20030227086 A1	Semiconductor device having multilevel copper wiring layers and its manufacture method
5			US 20030176056 A1	Method for forming metal wiring layer of semiconductor device
6			US 20030071361 A1	Structure and method for charge sensitive electrical devices
7			US 20020173143 A1	Method for forming metal wiring layer of semiconductor device
8			US 6815331 B2	Method for forming metal wiring layer of semiconductor device
9			US 6753610 B1	Semiconductor device having multilayer interconnection structure and method of making the same
10			US 6670717 B2	Structure and method for charge sensitive electrical devices

	U	1	Document ID	Title
11			JP 2000252278 A	SEMICONDUCTOR DEVICE AND ITS MANUFACTURE
12	X		JP 11297696 A	Wiring layer for large scale semiconductor integrated circuit - has barrier layer and copper layer doped with specific metallic impurity such that impurity concentration from boundary layer decreases
13	X		JP 10199881 A	Copper wiring covered semiconductor device manufacturing method - involves doping impurities having metal diffusion prevention capability on second insulating film covering wiring
14	X		JP 03289156 A	Semiconductor device mfr. - by forming copper wiring pattern on phosphorus-doped insulator covering substrate, and annealing substrate NoAbstract Dwg 1-3/5